

10/17/02

2811



Docket No. P0164US-7

Express Mailing Label No. EL815827761
PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants: PARIKH et al.

Examiner: Shouxiang Hu

Serial No. 09/911,155

Art Unit: 2811

Filing Date: July 23, 2001

For: GALLIUM NITRIDE BASED DIODES WITH LOW FORWARD VOLTAGE AND
LOW REVERSE CURRENT OPERATIONAssistant Commissioner for Patents
Washington, D.C. 20231AMENDMENT TRANSMITTAL

Sir:

Transmitted herewith is an amendment for this application. Applicant is a large entity.

Fee for Claims

	Claims Remaining After Amendment	Highest No. Previously Paid For	Present Extra	Rate	Addit. Fee
TOTAL	53	57	0	18.00	0.00
INDEP.	4	4	0	84.00	0.00

If any additional fee is required, charge Account No. 11-1580. A duplicate of this transmittal is attached.

Respectfully submitted,

October 15, 2002



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Attorney for Applicant

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Title: GALLIUM NITRIDE BASED DIODES WITH LOW FORWARD VOLTAGE AND LOW REVERSE CURRENT OPERATION

Assistant Commissioner for Patents
Washington, D.C. 20231

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AMENDMENT AND RESPONSE TO OFFICE ACTION

Sir:

On September 13, 2002, the Examiner issued a Response to Amendment in response to applicants' June 27, 2002, Amendment and Response to Office Action. The Examiner objected to the applicants' response as not being fully responsive and gave the applicants' 30 days to file a corrected response. Applicants hereby withdraw the June 27, 2002, Amendment and Response to Office Action, and amend the present application as follows:

Claims

Replace the corresponding claims in the original application with the following:

1. A diode, comprising:

an n+ doped GaN layer;

an n- doped GaN layer on said n+ GaN layer, the surface of said n- doped GaN layer having an unpinned Fermi level; and

a Schottky metal layer on said n- doped GaN layer having a work function, said n- GaN layer forming a

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